

NCE P-Channel Enhancement Mode Power MOSFET

Description

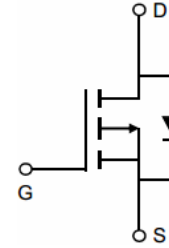
The NCE2305 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

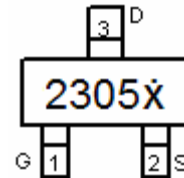
- $V_{DS} = -20V, I_D = -4.1A$
 $R_{DS(ON)} < 60m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 45m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Surface mount package
- Pb free terminal plating
- RoHS compliant
- Halogen free

Application

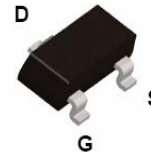
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2305 X	NCE2305	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	-5.4	A
	$T_C = 70^\circ C$		-4.3	
	$T_A = 25^\circ C$		-4.1	
	$T_A = 70^\circ C$		-3.2	
Drain Current -Pulsed (Note 1)		I_{DM}	-20	A
Maximum Power Dissipation	$T_C = 25^\circ C$	P_D	1.7	W
	$T_C = 70^\circ C$		1.1	
	$T_A = 25^\circ C$		1.0	
	$T_A = 70^\circ C$		0.65	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	125	$^\circ C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-20	-	-	V
Parameter						
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.45	-0.7	-1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4.1A	-	34	45	mΩ
		V _{GS} =-2.5V, I _D =-3A	-	44	60	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4.1A	-	6	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{ISS}	V _{DS} =-4V, V _{GS} =0V, F=1.0MHz	-	740	-	PF
Output Capacitance	C _{OSS}		-	290	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	190	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-4V, R _L =-1.2Ω, V _{GEN} =-4.5V, R _g =1Ω	-	12	-	nS
Turn-on Rise Time	t _r		-	35	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-4V, I _D =-4.1A, V _{GS} =-4.5V	-	7.8	-	nC
Gate-Source Charge	Q _{gs}		-	1.2	-	nC
Gate-Drain Charge	Q _{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-4.1A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-4.1	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

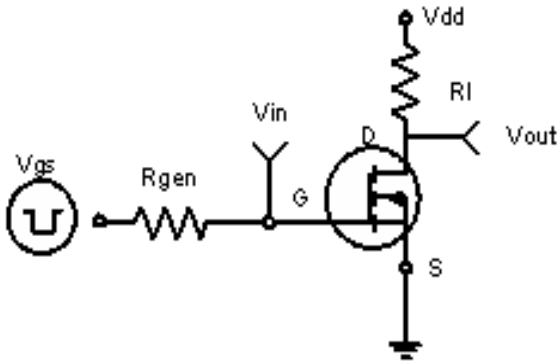


Figure 1: Switching Test Circuit

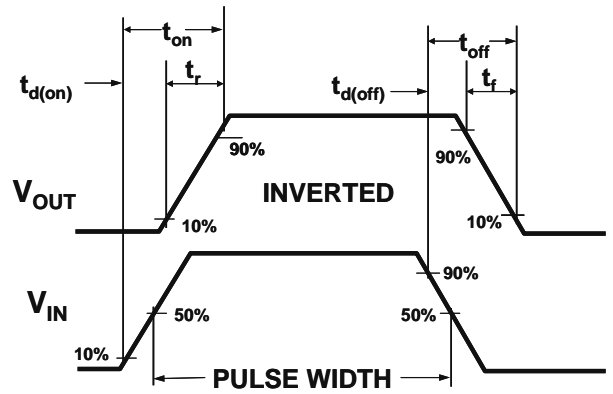
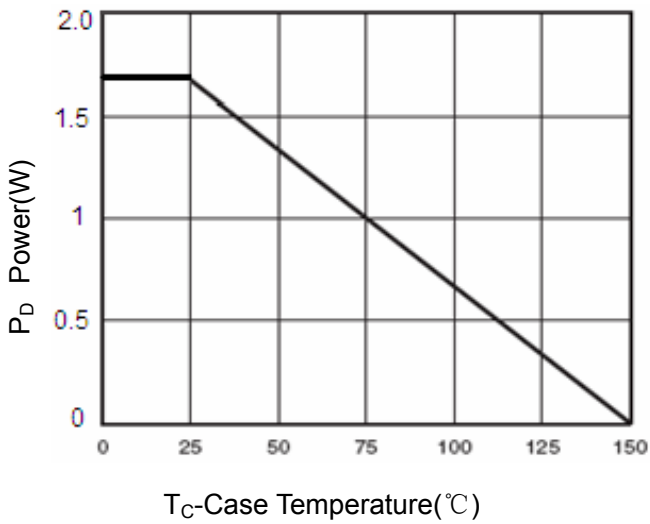
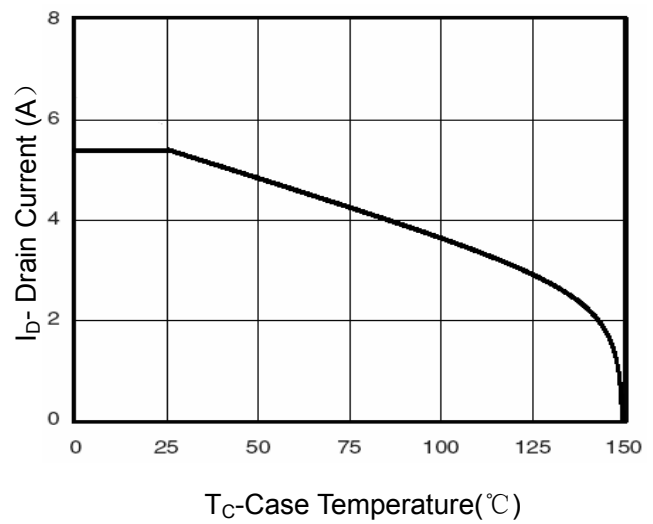


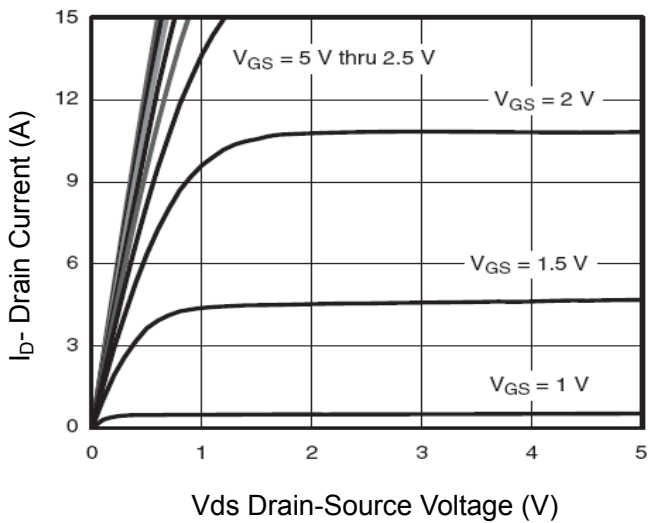
Figure 2: Switching Waveforms



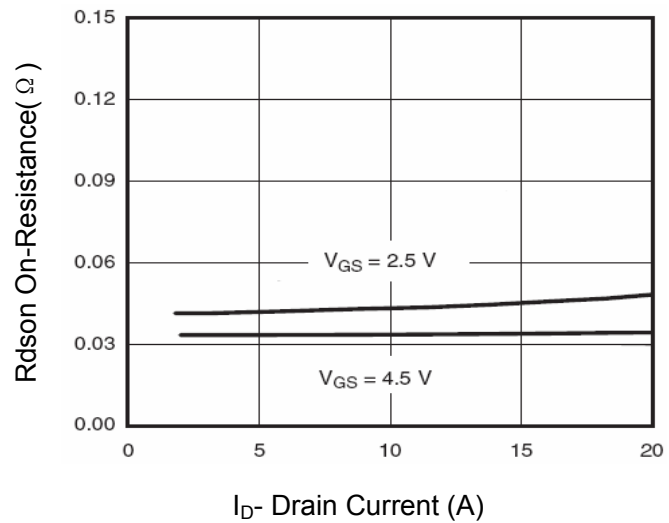
T_C-Case Temperature(°C)
Figure 3 Power Dissipation



T_C-Case Temperature(°C)
Figure 4 Drain Current



V_{ds} Drain-Source Voltage (V)
Figure 5 Output Characteristics



I_D- Drain Current (A)
Figure 6 Drain-Source On-Resistance

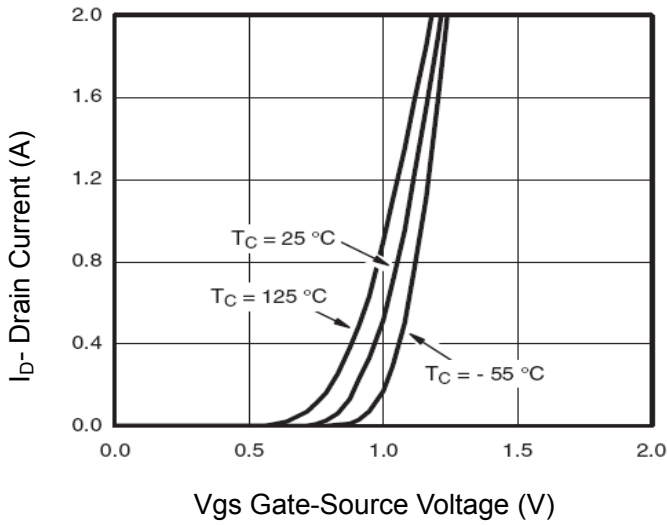


Figure 7 Transfer Characteristics

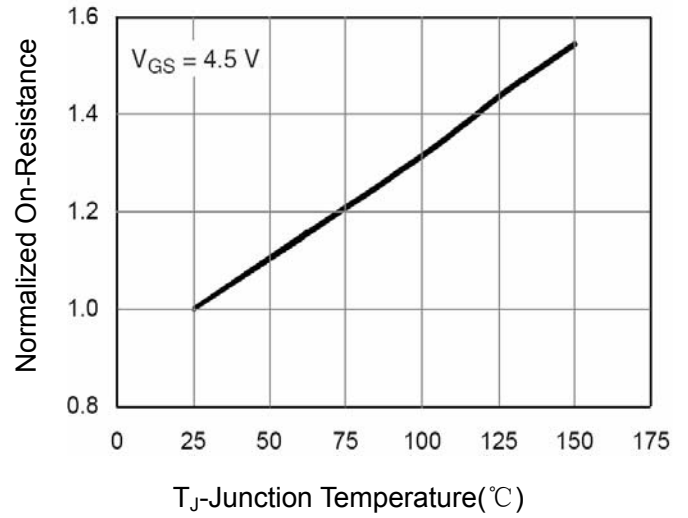


Figure 8 Drain-Source On-Resistance

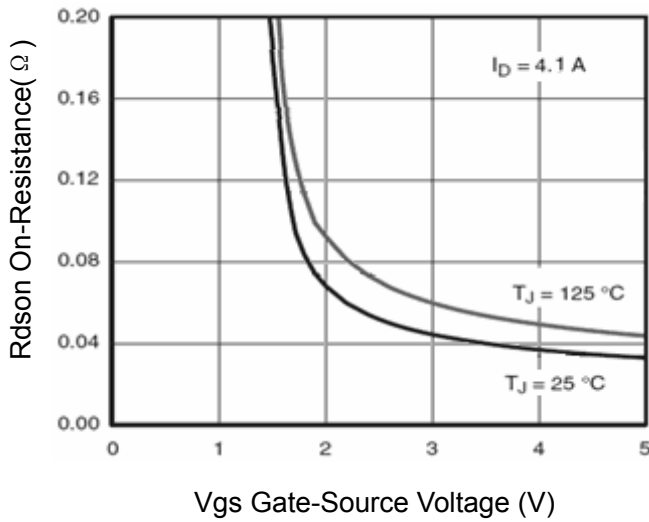


Figure 9 $R_{DS(on)}$ vs V_{GS}

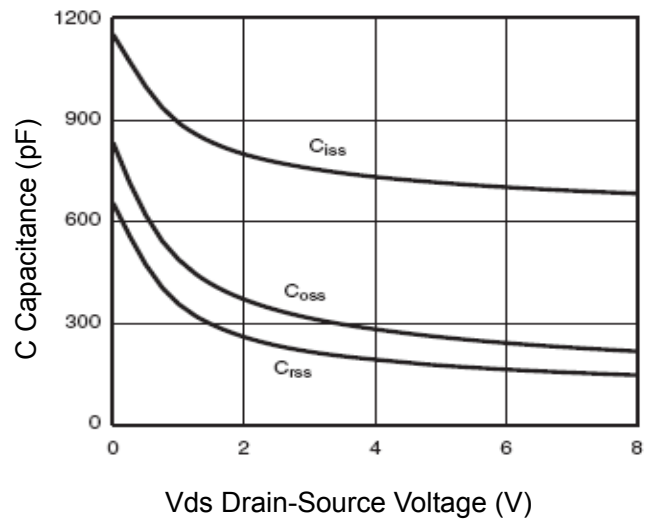


Figure 10 Capacitance vs V_{DS}

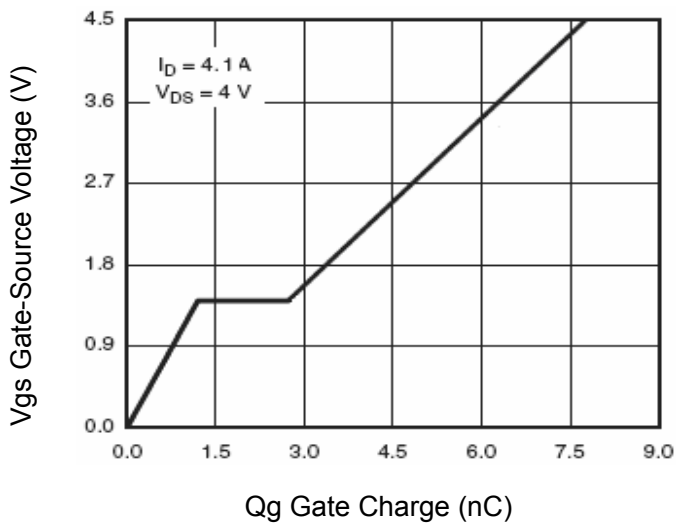


Figure 11 Gate Charge

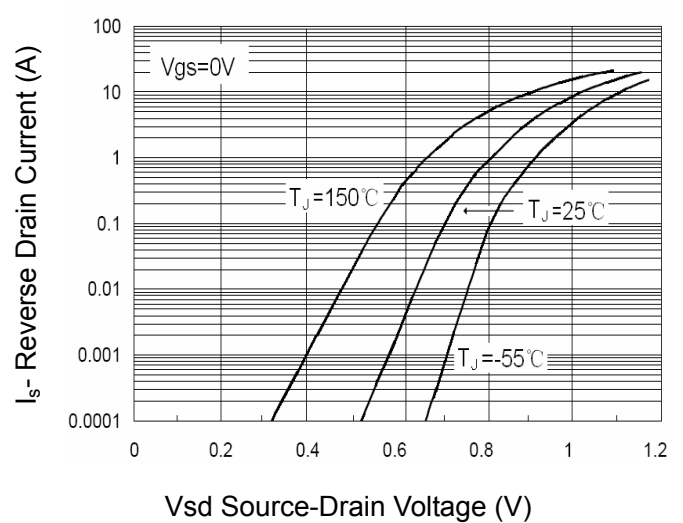
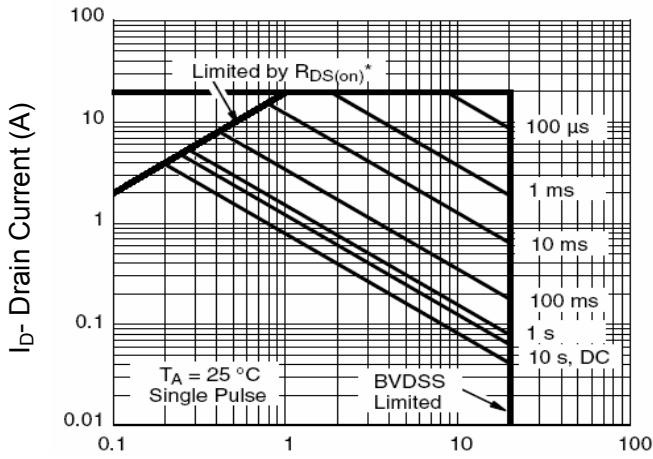
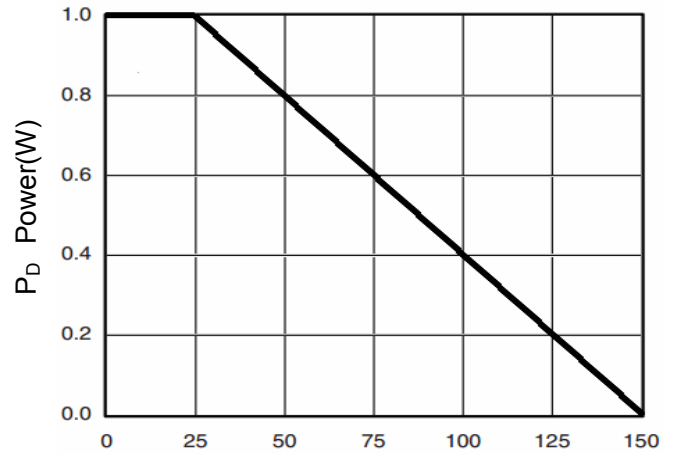


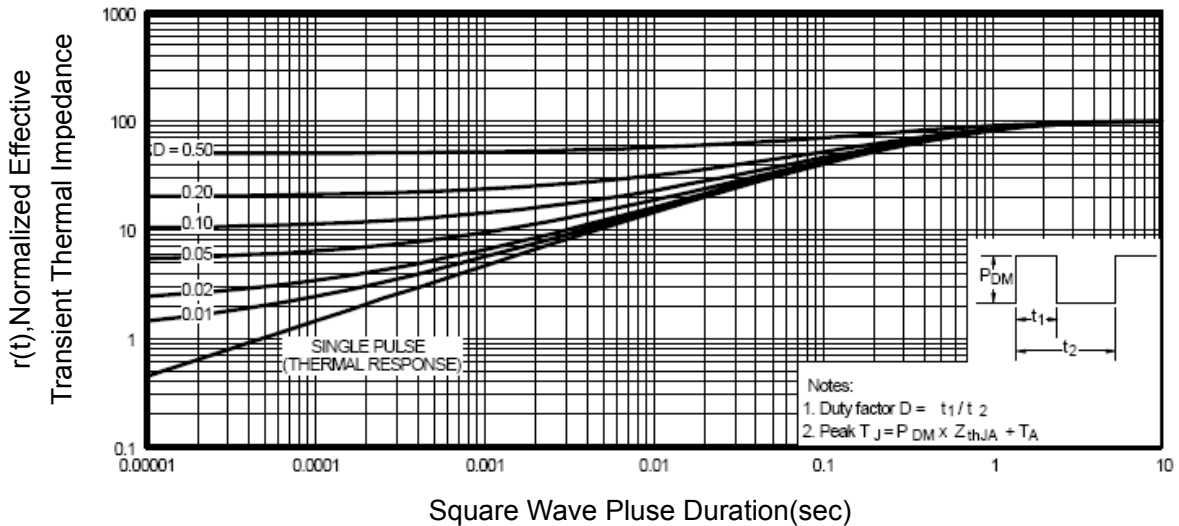
Figure 12 Source- Drain Diode Forward



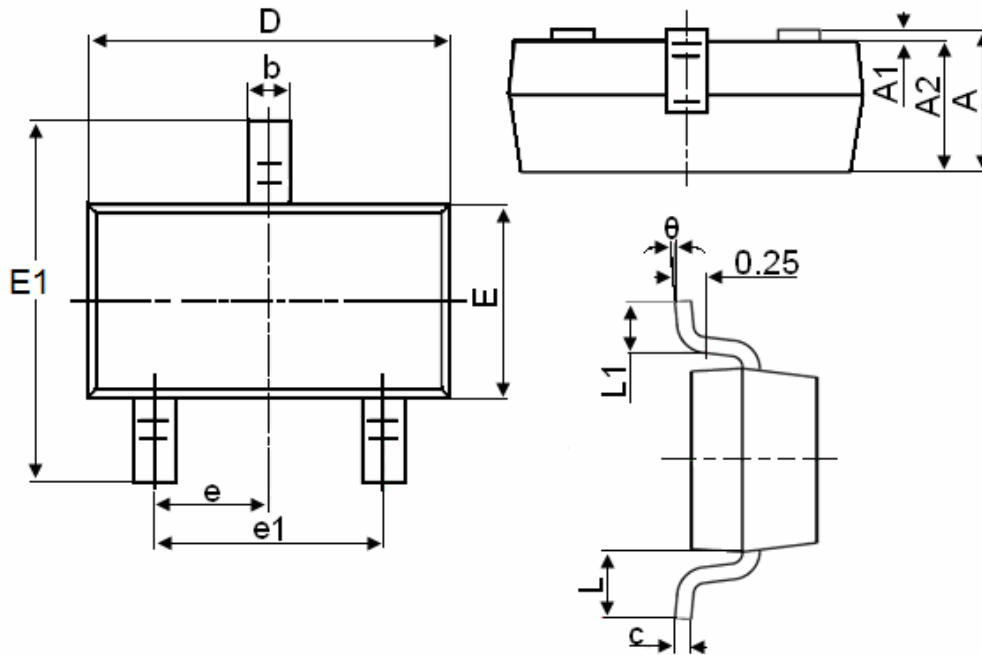
V_{ds} Drain-Source Voltage (V)
Figure 13 Safe Operation Area



T_A-Ambient Temperature(°C)
Figure 14 Power Dissipation



Square Wave Pulse Duration(sec)
Figure 15 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information


Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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